



NPN Digital Transistors (Built-in Resistors)



Features

- \* Built-in bias resistors enable the configuration of an inverter circuit without connecting input resistors (see equivalent circuit)
- \* Only the on/off conditions need to be set for operation, making device design easy.
- \* The bias resistors consist of thin film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.

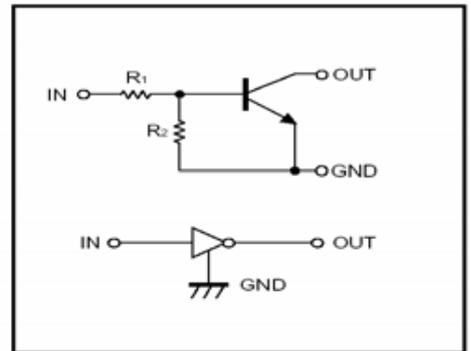
SOT-23



DEVICE MARKING AND RESISTOR VALUES

Device	Marking	R1(K)	R2(K)	Shipping
DTC144ECA	A8C / 26	47	47	3000/Tape&Reel

●Equivalent circuit



MAXIMUM RATINGS (T<sub>A</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current	I <sub>C</sub>	100	mAdc
Total Power Dissipation @ T <sub>A</sub> = 25°C (Note 1.) Derate above 25°C	P <sub>D</sub>	246 1.5	mW °C/W

1. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

# DEVICE CHARACTERISTICS

## DTC144ECA

### THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Resistance – Junction-to-Ambient (Note 1.)	$R_{\theta JA}$	508	°C/W
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	°C
Maximum Temperature for Soldering Purposes, Time in Solder Bath	$T_L$	260 10	°C Sec

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector-Base Cutoff Current ( $V_{CB} = 50\text{ V}, I_E = 0$ )	$I_{CBO}$	–	–	100	nAdc
Collector-Emitter Cutoff Current ( $V_{CE} = 50\text{ V}, I_B = 0$ )	$I_{CEO}$	–	–	500	nAdc
Emitter-Base Cutoff Current ( $V_{EB} = 6.0\text{ V}, I_C = 0$ )	$I_{EBO}$	–	–	0.1	mAdc
Collector-Base Breakdown Voltage ( $I_C = 10\ \mu\text{A}, I_E = 0$ )	$V_{(BR)CBO}$	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (Note 2.), ( $I_C = 2.0\text{ mA}, I_B = 0$ )	$V_{(BR)CEO}$	50	–	–	Vdc

### ON CHARACTERISTICS (Note 2.)

DC Current Gain ( $V_{CE} = 10\text{ V}, I_C = 5.0\text{ mA}$ )	$h_{FE}$	80	140	–	
Collector-Emitter Saturation Voltage ( $I_C = 10\text{ mA}, I_B = 0.3\text{ mA}$ )	$V_{CE(sat)}$	–	–	0.25	Vdc

2. Pulse Test: Pulse Width < 300  $\mu\text{s}$ , Duty Cycle < 2.0%.

### ON CHARACTERISTICS (Note 3.)

Output Voltage (on) ( $V_{CC} = 5.0\text{ V}, V_B = 3.5\text{ V}, R_L = 1.0\text{ k}\Omega$ )	$V_{OL}$	–	–	0.2	Vdc
Output Voltage (off) ( $V_{CC} = 5.0\text{ V}, V_B = 0.5\text{ V}, R_L = 1.0\text{ k}\Omega$ )	$V_{OH}$	4.9	–	–	Vdc
Input Resistor	$R_1$	32.9	47	61.1	$\text{k}\Omega$
Resistor Ratio	$R_1/R_2$	0.8	1.0	1.2	

3. Pulse Test: Pulse Width < 300  $\mu\text{s}$ , Duty Cycle < 2.0%.

# DEVICE CHARACTERISTICS

## DTC144ECA

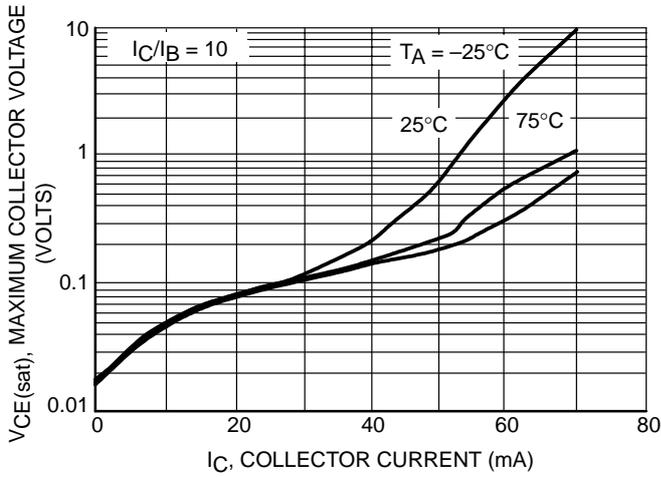


Figure 12.  $V_{CE(sat)}$  vs.  $I_C$

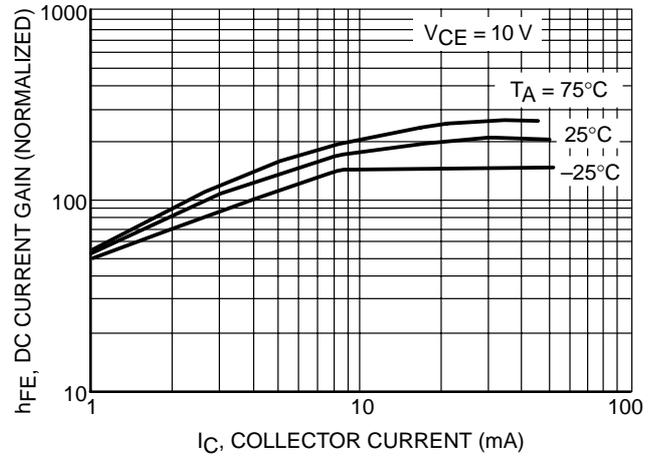


Figure 13. DC Current Gain

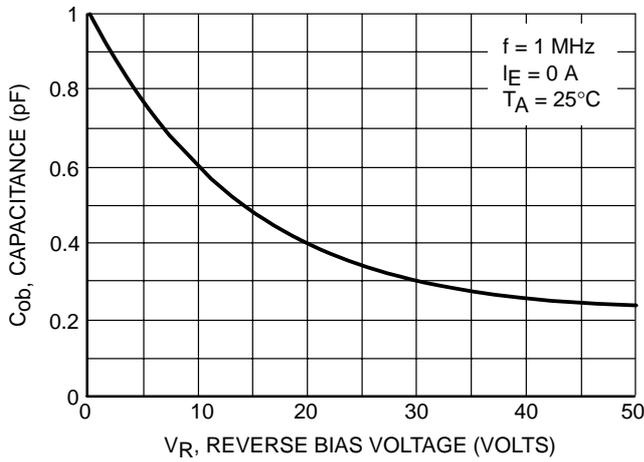


Figure 14. Output Capacitance

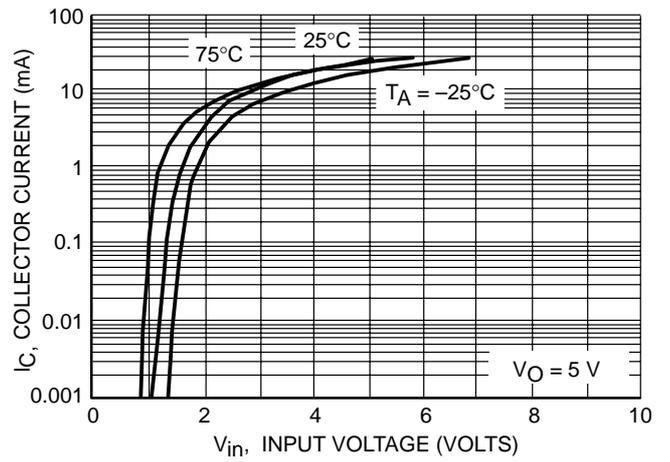


Figure 15. Output Current vs. Input Voltage

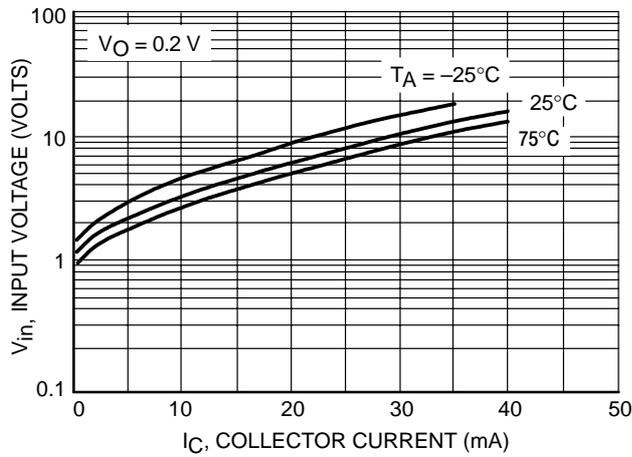
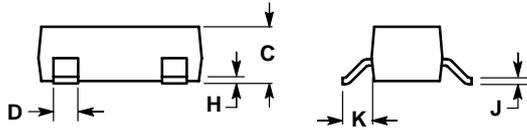
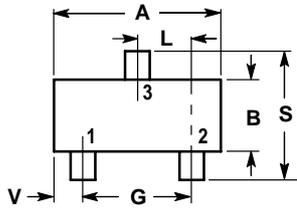


Figure 16. Input Voltage vs. Output Current

# PACKAGE OUTLINE & DIMENSIONS

## DTC144ECA

### SOT-23



#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

